

Amendment to the Specification:

Please replace the paragraph beginning on page 10, line 20 with the following amended paragraph:

A gate insulation pattern 119a is interposed between the selection gate electrode 121a and the control gate pattern 110, and the selection gate electrode 121a and the semiconductor substrate 101. The gate insulation pattern ~~109a~~ 119a may be elongated to cover the entire plane sidewall of the selection gate electrode ~~119a~~ 121a on the control gate pattern 110. In this case, the exposed sidewall of the control gate pattern 110 and the portion of the gate insulation pattern 119a disposed on the control gate pattern 110 may be disposed on the same vertical line.